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STATEMENT BY APPLICANT				First Named Inventor	Alexander Barr et al	
				Group Art Unit	2811	
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Sheet	1	of	1	Attorney Docket Number	SC13265TP	

				U. S. PATENT DOCUMENTS		
Examiner	Cite No.	U.S. Pa	atent Document	Name of Patentee or Applicant	Date of Publication of	Pages, Columns, Lines, Where Relevan Passages or Relevant Figures Appear
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	88	M. SHII Parasiti	M. SHIMA et al – "<100> Channel Strained – SiGe p-MOSFET with Enhanced Hole Mobility and Lower Parasitic Resistance" (2002 Symposium on VLSI Technology Digest of Technical Papers, pg 94-95							
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(A)	AC		LANGDO et al., "Preparation of Novel SiGe-Free Strained Si on Insulator Substrates," AMBERWAVE SYSTEMS CORP., SALEM, NH, 2 pgs.							
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0	AD .	<100>Channel for Embedde	ed RF/A	nalog Applic	ations,"	IEEE, pp. 663-	and High N 666 (2002)			
0	AE		SAYAMA et al., "Effect of <100> Channel Direction for High Performance SCE Immune pMOSFET with Less Than 0.15µm Gate Length," IEEE, 4 pgs., (1999).							

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pp. 52-57.

AOKI et al., "Optimum Crystallographic Orientation of Submicrometer CMOS Devices Operated at Low Temperatures," IEEE TRANSACTIONS ON ELECTRON DEVICES, VOL. ED-34, NO. 1, JANUARY 1987,

¹ Unique citation designation number. ² See Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WiPO Standard ST.3). ⁴ For Japanese patent documents the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WiPO Standard ST. 16 If possible. ⁶ Applicant is to place a check mark here if English Language Translation is attached.

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